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Understanding <u>Embedded - CPLDs (Complex Programmable Logic Devices)</u>

Embedded - CPLDs, or Complex Programmable Logic Devices, are highly versatile digital logic devices used in electronic systems. These programmable components are designed to perform complex logical operations and can be customized for specific applications. Unlike fixed-function ICs, CPLDs offer the flexibility to reprogram their configuration, making them an ideal choice for various embedded systems. They consist of a set of logic gates and programmable interconnects, allowing designers to implement complex logic circuits without needing custom hardware.

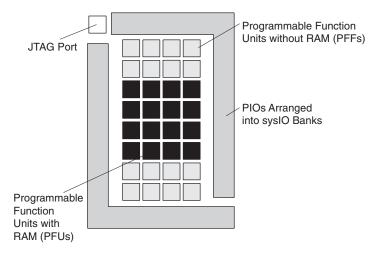
Applications of Embedded - CPLDs

Details	
Product Status	Active
Programmable Type	In System Programmable
Delay Time tpd(1) Max	4.9 ns
Voltage Supply - Internal	1.14V ~ 1.26V
Number of Logic Elements/Blocks	-
Number of Macrocells	320
Number of Gates	-
Number of I/O	159
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	256-LBGA
Supplier Device Package	256-FTBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lamxo640e-3ftn256e

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Figure 2-3. Top View of the LA-MachXO256 Device

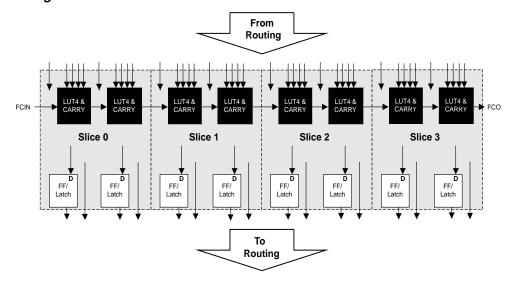


PFU Blocks

The core of the LA-MachXO devices consists of PFU and PFF blocks. The PFUs can be programmed to perform Logic, Arithmetic, Distributed RAM, and Distributed ROM functions. PFF blocks can be programmed to perform Logic, Arithmetic, and Distributed ROM functions. Except where necessary, the remainder of this data sheet will use the term PFU to refer to both PFU and PFF blocks.

Each PFU block consists of four interconnected Slices, numbered 0-3 as shown in Figure 2-4. There are 53 inputs and 25 outputs associated with each PFU block.

Figure 2-4. PFU Diagram



Slice

Each Slice contains two LUT4 lookup tables feeding two registers (programmed to be in FF or Latch mode), and some associated logic that allows the LUTs to be combined to perform functions such as LUT5, LUT6, LUT7, and LUT8. There is control logic to perform set/reset functions (programmable as synchronous/asynchronous), clock select, chip-select, and wider RAM/ROM functions. Figure 2-5 shows an overview of the internal logic of the Slice. The registers in the Slice can be configured for positive/negative and edge/level clocks.

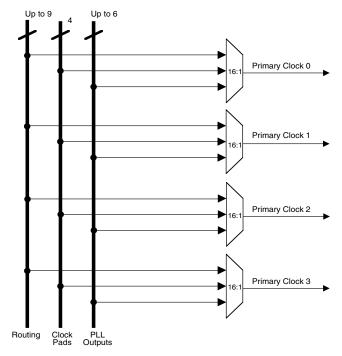


Figure 2-8. Primary Clocks for LA-MachXO1200 and LA-MachXO2280 Devices

Four secondary clocks are generated from four 16:1 muxes as shown in Figure 2-9. Four of the secondary clock sources come from dual function clock pins and 12 come from internal routing.

Figure 2-9. Secondary Clocks for LA-MachXO Devices

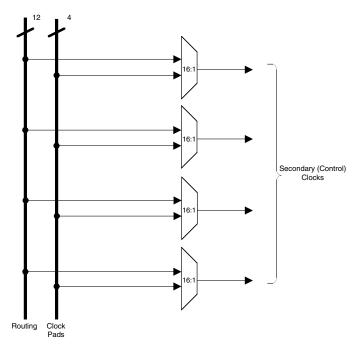
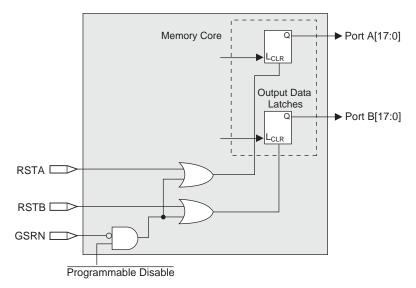


Figure 2-13. Memory Core Reset

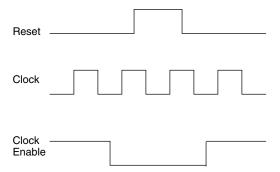


For further information on the sysMEM EBR block, see the details of additional technical documentation at the end of this data sheet.

EBR Asynchronous Reset

EBR asynchronous reset or GSR (if used) can only be applied if all clock enables are low for a clock cycle before the reset is applied and released a clock cycle after the reset is released, as shown in Figure 2-14. The GSR input to the EBR is always asynchronous.

Figure 2-14. EBR Asynchronous Reset (Including GSR) Timing Diagram



If all clock enables remain enabled, the EBR asynchronous reset or GSR may only be applied and released after the EBR read and write clock inputs are in a steady state condition for a minimum of 1/f_{MAX} (EBR clock). The reset release must adhere to the EBR synchronous reset setup time before the next active read or write clock edge.

If an EBR is pre-loaded during configuration, the GSR input must be disabled or the release of the GSR during device Wake Up must occur before the release of the device I/Os becoming active.

These instructions apply to all EBR RAM, ROM and FIFO implementations. For the EBR FIFO mode, the GSR signal is always enabled and the WE and RE signals act like the clock enable signals in Figure 2-14. The reset timing rules apply to the RPReset input vs the RE input and the RST input vs. the WE and RE inputs. Both RST and RPReset are always asynchronous EBR inputs.

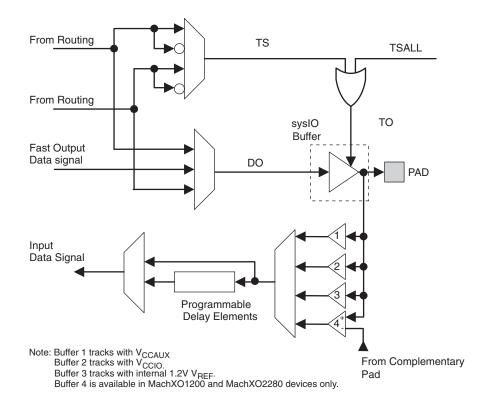
Note that there are no reset restrictions if the EBR synchronous reset is used and the EBR GSR input is disabled.

output data signals are multiplexed and provide a single signal to the I/O pin via the sysIO buffer. Figure 2-17 shows the LA-MachXO PIO logic.

The tristate control signal is multiplexed from the output data signals and their complements. In addition a global signal (TSALL) from a dedicated pad can be used to tristate the sysIO buffer.

The PIO receives an input signal from the pin via the sysIO buffer and provides this signal to the core of the device. In addition there are programmable elements that can be utilized by the design tools to avoid positive hold times.

Figure 2-17. LA-MachXO PIO Block Diagram



sysIO Buffer

Each I/O is associated with a flexible buffer referred to as a sysIO buffer. These buffers are arranged around the periphery of the device in groups referred to as Banks. The sysIO buffers allow users to implement the wide variety of standards that are found in today's systems including LVCMOS, TTL, BLVDS, LVDS and LVPECL.

In the LA-MachXO devices, single-ended output buffers and ratioed input buffers (LVTTL, LVCMOS and PCI) are powered using V_{CCIO} . In addition to the Bank V_{CCIO} supplies, the LA-MachXO devices have a V_{CC} core logic power supply, and a V_{CCAUX} supply that powers up a variety of internal circuits including all the differential and referenced input buffers.

LA-MachXO256 and LA-MachXO640 devices contain single-ended input buffers and single-ended output buffers with complementary outputs on all the I/O Banks.

LA-MachXO1200 and LA-MachXO2280 devices contain two types of sysIO buffer pairs.

1. Top and Bottom sysIO Buffer Pairs

The sysIO buffer pairs in the top and bottom Banks of the device consist of two single-ended output drivers and two sets of single-ended input buffers (for ratioed or absolute input levels). The I/O pairs on the top and bottom

Table 2-8. I/O Support Device by Device

	LA-MachXO256	LA-MachXO640	LA-MachXO1200	LA-MachXO2280
Number of I/O Banks	2	4	8	8
Type of Input Buffers	Single-ended (all I/O Banks)	Single-ended (all I/O Banks)	Single-ended (all I/O Banks) Differential Receivers	Single-ended (all I/O Banks) Differential Receivers
	0: 1 11 "	0: 1 11 "	(all I/O Banks)	(all I/O Banks)
Types of Output Buffers	Single-ended buffers with complementary outputs (all I/O Banks)	Single-ended buffers with complementary outputs (all I/O Banks)	Single-ended buffers with complementary outputs (all I/O Banks)	Single-ended buffers with complementary outputs (all I/O Banks)
			Differential buffers with true LVDS outputs (50% on left and right side)	Differential buffers with true LVDS outputs (50% on left and right side)
Differential Output Emulation Capability	All I/O Banks	All I/O Banks	All I/O Banks	All I/O Banks
PCI Support	No	No	Top side only	Top side only

Table 2-9. Supported Input Standards

	VCCIO (Typ.)					
Input Standard	3.3V	2.5V	1.8V	1.5V	1.2V	
Single Ended Interfaces						
LVTTL	V	V	V	√	V	
LVCMOS33	V	V	V	√	V	
LVCMOS25	V	V	V	√	V	
LVCMOS18			√			
LVCMOS15				√		
LVCMOS12	V	V	V	√	V	
PCI ¹	√					
Differential Interfaces	•	•				
BLVDS ² , LVDS ² , LVPECL ² , RSDS ²	V	V	V	V	V	

^{1.} Top Banks of LA-MachXO1200 and LA-MachXO2280 devices only.

^{2.} LA-MachXO1200 and LA-MachXO2280 devices only.

Table 2-10. Supported Output Standards

Output Standard	Drive	V _{CCIO} (Typ.)
Single-ended Interfaces		
LVTTL	4mA, 8mA, 12mA, 16mA	3.3
LVCMOS33	4mA, 8mA, 12mA, 14mA	3.3
LVCMOS25	4mA, 8mA, 12mA, 14mA	2.5
LVCMOS18	4mA, 8mA, 12mA, 14mA	1.8
LVCMOS15	4mA, 8mA	1.5
LVCMOS12	2mA, 6mA	1.2
LVCMOS33, Open Drain	4mA, 8mA, 12mA, 14mA	_
LVCMOS25, Open Drain	4mA, 8mA, 12mA, 14mA	_
LVCMOS18, Open Drain	4mA, 8mA, 12mA, 14mA	_
LVCMOS15, Open Drain	4mA, 8mA	_
LVCMOS12, Open Drain	2mA, 6mA	_
PCI33 ³	N/A	3.3
Differential Interfaces		
LVDS ^{1, 2}	N/A	2.5
BLVDS, RSDS ²	N/A	2.5
LVPECL ²	N/A	3.3

^{1.} LA-MachXO1200 and LA-MachXO2280 devices have dedicated LVDS buffers.

sysIO Buffer Banks

The number of Banks vary between the devices of this family. Eight Banks surround the two larger devices, the LA-MachXO1200 and LA-MachXO2280 (two Banks per side). The LA-MachXO640 has four Banks (one Bank per side). The smallest member of this family, the LA-MachXO256, has only two Banks.

Each sysIO buffer Bank is capable of supporting multiple I/O standards. Each Bank has its own I/O supply voltage (V_{CCIO}) which allows it to be completely independent from the other Banks. Figure 2-18, Figure 2-18, Figure 2-20 and Figure 2-21 shows the sysIO Banks and their associated supplies for all devices.

^{2.} These interfaces can be emulated with external resistors in all devices.

^{3.} Top Banks of LA-MachXO1200 and LA-MachXO2280 devices only.



LA-MachXO Automotive Family Data Sheet Onductor DC and Switching Characteristics

November 2007 Data Sheet DS1003

Absolute Maximum Ratings^{1, 2, 3}

	LCMXO E (1.2V)	LCMXO C (1.8V/2.5V/3.3V)
Supply Voltage V _{CC}	0.5 to 1.32V	0.5 to 3.75V
Supply Voltage V _{CCAUX}	0.5 to 3.75V	0.5 to 3.75V
Output Supply Voltage V_{CCIO}	0.5 to 3.75V	0.5 to 3.75V
I/O Tristate Voltage Applied 4	0.5 to 3.75V	0.5 to 3.75V
Dedicated Input Voltage Applied ⁴	0.5 to 3.75V	0.5 to 4.25V
Storage Temperature (ambient)	65 to 150°C	65 to 150°C
Junction Temp. (Tj)	+125°C	+125°C

^{1.} Stress above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Recommended Operating Conditions¹

Symbol	Parameter		Max.	Units
V	Core Supply Voltage for 1.2V Devices	1.14	1.26	V
V _{CC}	Core Supply Voltage for 1.8V/2.5V/3.3V Devices	1.71	3.465	V
V _{CCAUX} ³	Auxiliary Supply Voltage	3.135	3.465	V
V _{CCIO} ²	I/O Driver Supply Voltage		3.465	V
t _{JAUTO}	Junction Temperature Automotive Operation	-40	125	ç
t _{JFLASHAUTO}	Junction Temperature, Flash Programming, Automotive	-40	125	°C

Like power supplies must be tied together. For example, if V_{CCIO} and V_{CC} are both 2.5V, they must also be the same supply. 3.3V V_{CCIO} and 1.2V V_{CCIO} should be tied to V_{CCAUX} or 1.2V V_{CC} respectively.

LA-MachXO256 and LA-MachXO640 Hot Socketing Specifications^{1,2,3}

Symbol	Parameter	Condition	Min.	Тур.	Max	Units
I _{DK}	Input or I/O leakage Current	$0 \le V_{IN} \le V_{IH} (MAX)$			+/-1000	μΑ

^{1.} Insensitive to sequence of $V_{CC,}V_{CCAUX,}$ and $V_{CCIO.}$ However, assumes monotonic rise/fall rates for $V_{CC,}V_{CCAUX,}$ and $V_{CCIO.}$

^{2.} Compliance with the Lattice Thermal Management document is required.

^{3.} All voltages referenced to GND.

^{4.} Overshoot and undershoot of -2V to (V_{IHMAX} + 2) volts is permitted for a duration of <20ns.

^{2.} See recommended voltages by I/O standard in subsequent table.

^{3.} V_{CC} must reach minimum V_{CC} value before V_{CCAUX} reaches 2.5V.

^{2.} $0 \le V_{CC} \le V_{CC}$ (MAX), $0 \le V_{CCIO} \le V_{CCIO}$ (MAX) and $0 \le V_{CCAUX} \le V_{CCAUX}$ (MAX).

^{3.} I_{DK} is additive to I_{PU}, I_{PD} or I_{BH}.

LA-MachXO1200 and LA-MachXO2280 Hot Socketing Specifications^{1, 2, 3, 4}

Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
Non-LVDS General Purpose syslOs						
I _{DK}	Input or I/O Leakage Current	$0 \le V_{IN} \le V_{IH} (MAX.)$	_	_	+/-1000	μA
LVDS General Purpose syslOs						
lau waa	Input or I/O Leakage Current	V _{IN} ≤ V _{CCIO}	_	_	+/-1000	μΑ
Input or I/O Leakage Current		$V_{IN} > V_{CCIO}$	_	35	_	mA

- 1. Insensitive to sequence of $V_{CC, V_{CCAUX}}$, and V_{CCIO} . However, assumes monotonic rise/fall rates for $V_{CC, V_{CCAUX}}$, and V_{CCIO} . 2. $0 \le V_{CC} \le V_{CC}$ (MAX), $0 \le V_{CCIO} \le V_{CCIO}$ (MAX), and $0 \le V_{CCAUX} \le V_{CCAUX}$ (MAX).
- 3. I_{DK} is additive to I_{PU} , I_{PW} or I_{BH} .
- 4. LVCMOS and LVTTL only.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
I _{IL,} I _{IH} 1, 4, 5	Input or I/O Leakage	$0 \le V_{IN} \le (V_{CCIO} - 0.2V)$	_	_	10	μΑ
I'IL, 'IH	linput of 1/O Leakage	$(V_{CCIO} - 0.2V) < V_{IN} \le 3.6V$	_	_	40	μΑ
I _{PU}	I/O Active Pull-up Current	$0 \le V_{IN} \le 0.7 V_{CCIO}$	-30	_	-150	μΑ
I _{PD}	I/O Active Pull-down Current	V_{IL} (MAX) $\leq V_{IN} \leq V_{IH}$ (MAX)	30	_	150	μΑ
I _{BHLS}	Bus Hold Low sustaining current	$V_{IN} = V_{IL} (MAX)$	30		_	μΑ
I _{BHHS}	Bus Hold High sustaining current	$V_{IN} = 0.7V_{CCIO}$	-30	_	_	μΑ
I _{BHLO}	Bus Hold Low Overdrive current	$0 \le V_{IN} \le V_{IH} (MAX)$	_	_	150	μΑ
I _{BHHO}	Bus Hold High Overdrive current	$0 \le V_{IN} \le V_{IH} (MAX)$	_		-150	μΑ
V _{BHT} ³	Bus Hold trip Points	$0 \le V_{IN} \le V_{IH} (MAX)$	V _{IL} (MAX)	_	V _{IH} (MIN)	V
C1	I/O Capacitance ²	$V_{CCIO} = 3.3V$, 2.5V, 1.8V, 1.5V, 1.2V, $V_{CC} = Typ.$, $V_{IO} = 0$ to V_{IH} (MAX)	_	8	_	pf
C2	Dedicated Input Capacitance ²	$V_{CCIO} = 3.3V$, 2.5V, 1.8V, 1.5V, 1.2V, $V_{CC} = Typ.$, $V_{IO} = 0$ to V_{IH} (MAX)	_	8	_	pf

^{1.} Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.

- 2. T_A 25°C, f = 1.0MHz
- 3. Please refer to V_{IL} and V_{IH} in the sysIO Single-Ended DC Electrical Characteristics table of this document.
- 4. Not applicable to SLEEPN pin.
- 5. When VIH is higher than VCCIO, a transient current typically of 30ns in duration or less with a peak current of 6mA can occur on the high-tolow transition. For LA-MachXO1200 and LA-MachXO2280 true LVDS output pins, VIH must be less than or equal to VCIIO.

sysIO Recommended Operating Conditions

	V _{CCIO} (V)			
Standard	Min.	Тур.	Max.	
LVCMOS 3.3	3.135	3.3	3.465	
LVCMOS 2.5	2.375	2.5	2.625	
LVCMOS 1.8	1.71	1.8	1.89	
LVCMOS 1.5	1.425	1.5	1.575	
LVCMOS 1.2	1.14	1.2	1.26	
LVTTL	3.135	3.3	3.465	
PCI ³	3.135	3.3	3.465	
LVDS ^{1, 2}	2.375	2.5	2.625	
LVPECL1	3.135	3.3	3.465	
BLVDS ¹	2.375	2.5	2.625	
RSDS ¹	2.375	2.5	2.625	

^{1.} Inputs on chip. Outputs are implemented with the addition of external resistors.

^{2.} MachXO1200 and MachXO2280 devices have dedicated LVDS buffers

^{3.} Input on the top bank of the MachXO1200 and MachXO2280 only.

sysIO Differential Electrical Characteristics LVDS

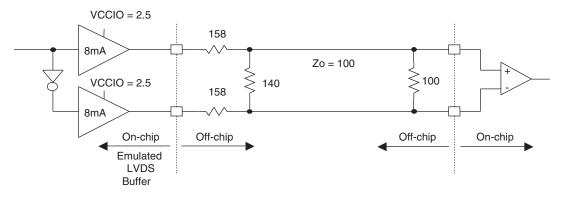
Over Recommended Operating Conditions

Parameter Symbol	Parameter Description	Test Conditions	Min.	Тур.	Max.	Units
V _{INP,} V _{INM}	Input Voltage		0	_	2.4	V
V_{THD}	Differential Input Threshold		+/-100		_	mV
		100mV ≤ V _{THD}	V _{THD} /2	1.2	1.8	V
V_{CM}	Input Common Mode Voltage	200mV ≤ V _{THD}	V _{THD} /2	1.2	1.9	V
		350mV ≤ V _{THD}	V _{THD} /2	1.2	2.0	V
I _{IN}	Input current	Power on	_	_	+/-10	μΑ
V _{OH}	Output high voltage for V _{OP} or V _{OM}	R _T = 100 Ohm	_	1.38	1.60	V
V_{OL}	Output low voltage for V _{OP} or V _{OM}	R _T = 100 Ohm	0.9V	1.03	_	V
V _{OD}	Output voltage differential	$(V_{OP} - V_{OM}), R_T = 100 Ohm$	250	350	450	mV
ΔV _{OD}	Change in V _{OD} between high and low		_	_	50	mV
V _{OS}	Output voltage offset	$(V_{OP} - V_{OM})/2$, $R_T = 100 \text{ Ohm}$	1.125	1.25	1.375	V
ΔV _{OS}	Change in V _{OS} between H and L		_	_	50	mV
I _{OSD}	Output short circuit current	V _{OD} = 0V Driver outputs shorted	_	_	6	mA

LVDS Emulation

LA-MachXO automotive devices can support LVDS outputs via emulation (LVDS25E), in addition to the LVDS support that is available on-chip on certain devices. The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all devices. The scheme shown in Figure 3-1 is one possible solution for LVDS standard implementation. Resistor values in Figure 3-1 are industry standard values for 1% resistors.

Figure 3-1. LVDS Using External Resistors (LVDS25E)



Note: All resistors are $\pm 1\%$.

The LVDS differential input buffers are available on certain devices in the LA-MachXO family.

Table 3-1. LVDS DC Conditions

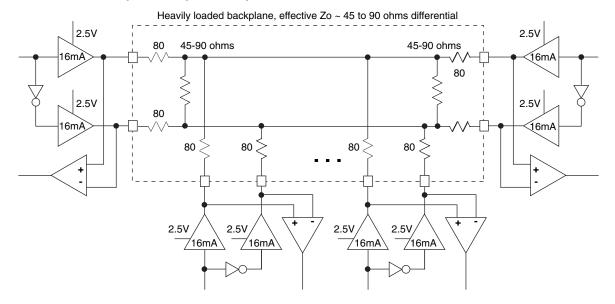
Over Recommended Operating Conditions

Parameter	Description	Typical	Units
Z _{OUT}	Output impedance	20	Ω
R _S	Driver series resistor	294	Ω
R _P	Driver parallel resistor	121	Ω
R _T	Receiver termination	100	Ω
V _{OH}	Output high voltage	1.43	V
V _{OL}	Output low voltage	1.07	V
V _{OD}	Output differential voltage	0.35	V
V _{CM}	Output common mode voltage	1.25	V
Z _{BACK}	Back impedance	100	Ω
I _{DC}	DC output current	3.66	mA

BLVDS

The LA-MachXO automotive family supports the BLVDS standard through emulation. The output is emulated using complementary LVCMOS outputs in conjunction with a parallel external resistor across the driver outputs. The input standard is supported by the LVDS differential input buffer on certain devices. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.

Figure 3-2. BLVDS Multi-point Output Example



Typical Building Block Function Performance¹

Pin-to-Pin Performance (LVCMOS25 12mA Drive)

Function	-3 Timing	Units
Basic Functions		
16-bit decoder	9.4	ns
4:1 MUX	6.3	ns
16:1 MUX	7.1	ns

Register-to-Register Performance

Function	-3 Timing	Units
Basic Functions		
16:1 MUX	348	MHz
16-bit adder	209	MHz
16-bit counter	277	MHz
64-bit counter	143	MHz
Embedded Memory Functions (12	00 and 2280 Devices Only)	
256x36 Single Port RAM	203	MHz
512x18 True-Dual Port RAM	203	MHz
Distributed Memory Functions		
16x2 Single Port RAM	310	MHz
64x2 Single Port RAM	229	MHz
128x4 Single Port RAM	186	MHz
32x2 Pseudo-Dual Port RAM	224	MHz
64x4 Pseudo-Dual Port RAM	194	MHz

The above timing numbers are generated using the ispLEVER design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.
 Rev. A 0.19

Derating Logic Timing

Logic Timing provided in the following sections of the data sheet and the ispLEVER design tools are worst case numbers in the operating range. Actual delays may be much faster. The ispLEVER design tool from Lattice can provide logic timing numbers at a particular temperature and voltage.

sysCLOCK PLL Timing

Over Recommended Operating Conditions

Descriptions	Conditions	Min.	Max.	Units
Input Clock Frequency (CLKI, CLKFB)		25	420	MHz
Output Clock Frequency (CLKOP, CLKOS)		25	420	MHz
K-Divider Output Frequency (CLKOK)		0.195	210	MHz
PLL VCO Frequency		420	840	MHz
Phase Detector Input Frequency		25	_	MHz
eristics		•		
Output Clock Duty Cycle	Default duty cycle selected ³	45	55	%
Output Phase Accuracy		_	0.05	UI
Output Clask Pariod litter	Fout ≥ 100MHz	_	+/-120	ps
Output Clock Period Jitter	Fout < 100MHz	T —	0.02	UIPP
Input Clock to Output Clock Skew	Divider ratio = integer	_	+/-200	ps
Output Clock Pulse Width	At 90% or 10% ³	1	_	ns
PLL Lock-in Time		_	150	μs
Programmable Delay Unit		100	450	ps
Input Clock Period Jitter		_	+/-200	ps
External Feedback Delay		_	10	ns
Input Clock High Time	90% to 90%	0.5	_	ns
Input Clock Low Time	10% to 10%	0.5	_	ns
RST Pulse Width		10	_	ns
	Input Clock Frequency (CLKI, CLKFB) Output Clock Frequency (CLKOP, CLKOS) K-Divider Output Frequency (CLKOK) PLL VCO Frequency Phase Detector Input Frequency Pristics Output Clock Duty Cycle Output Phase Accuracy Output Clock Period Jitter Input Clock to Output Clock Skew Output Clock Pulse Width PLL Lock-in Time Programmable Delay Unit Input Clock Period Jitter External Feedback Delay Input Clock High Time Input Clock Low Time	Input Clock Frequency (CLKI, CLKFB) Output Clock Frequency (CLKOP, CLKOS) K-Divider Output Frequency (CLKOK) PLL VCO Frequency Phase Detector Input Frequency Pristics Output Clock Duty Cycle Output Phase Accuracy Output Clock Period Jitter Input Clock to Output Clock Skew Divider ratio = integer Output Clock Pulse Width At 90% or 10%³ PLL Lock-in Time Programmable Delay Unit Input Clock Period Jitter External Feedback Delay Input Clock High Time Po% to 90% Input Clock Low Time	Input Clock Frequency (CLKI, CLKFB) 25	Input Clock Frequency (CLKI, CLKFB) 25 420 Output Clock Frequency (CLKOP, CLKOS) 25 420 K-Divider Output Frequency (CLKOK) 0.195 210 PLL VCO Frequency 420 840 Phase Detector Input Frequency 25 — ristics Output Clock Duty Cycle Default duty cycle selected³ 45 55 Output Phase Accuracy — 0.05 Output Clock Period Jitter Fout ≥ 100MHz — +/-120 Fout < 100MHz

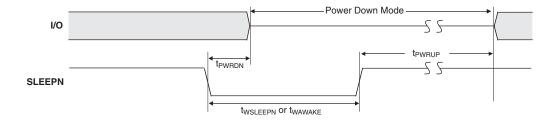
- 1. Jitter sample is taken over 10,000 samples of the primary PLL output with a clean reference clock.
- 2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
- 3. Using LVDS output buffers.
- 4. CLKOS as compared to CLKOP output.

Rev. A 0.19

LA-MachXO "C" Sleep Mode Timing

Symbol	Parameter	Device	Min.	Тур.	Max	Units
t _{PWRDN}	SLEEPN Low to Power Down	All	_	_	400	ns
t _{PWRUP} SLEEPN High to Po	SI EEDNI High to Power Up	LCMXO256	_	_	400	μs
	SEEFIN High to Fower op	LCMXO640	_	_	600	μs
t _{WSLEEPN}	SLEEPN Pulse Width	All	400	_	_	ns
twawake	SLEEPN Pulse Rejection	All	_	_	100	ns

Rev. A 0.19



LA-MachXO256 and LA-MachXO640 Logic Signal Connections: 100 TQFP

		LAM	XO256		LAMXO640				
Pin Number	Ball Function	Bank	Dual Function	Differential	Ball Function	Bank	Dual Function	Differential	
1	PL2A	1		Т	PL2A	3		Т	
2	PL2B	1		С	PL2C	3		Т	
3	PL3A	1		Т	PL2B	3		С	
4	PL3B	1		С	PL2D	3		С	
5	PL3C	1		Т	PL3A	3		Т	
6	PL3D	1		С	PL3B	3		С	
7	PL4A	1		Т	PL3C	3		Т	
8	PL4B	1		С	PL3D	3		С	
9	PL5A	1		Т	PL4A	3			
10	VCCIO1	1			VCCIO3	3			
11	PL5B	1		С	PL4C	3		Т	
12	GNDIO1	1			GNDIO3	3			
13	PL5C	1		Т	PL4D	3		С	
14	PL5D	1	GSRN	С	PL5B	3	GSRN		
15	PL6A	1		Т	PL7B	3			
16	PL6B	1	TSALL	С	PL8C	3	TSALL	Т	
17	PL7A	1		Т	PL8D	3		С	
18	PL7B	1		С	PL9A	3			
19	PL7C	1		Т	PL9C	3			
20	PL7D	1		С	PL10A	3			
21	PL8A	1		Т	PL10C	3			
22	PL8B	1		С	PL11A	3			
23	PL9A	1		Т	PL11C	3			
24	VCCIO1	1			VCCIO3	3			
25	GNDIO1	1			GNDIO3	3			
26	TMS	1	TMS		TMS	2	TMS		
27	PL9B	1		С	PB2C	2			
28	TCK	1	TCK		TCK	2	TCK		
29	PB2A	1		Т	VCCIO2	2			
30	PB2B	1		С	GNDIO2	2			
31	TDO	1	TDO		TDO	2	TDO		
32	PB2C	1		Т	PB4C	2			
33	TDI	1	TDI		TDI	2	TDI		
34	PB2D	1		С	PB4E	2			
35	VCC	-			VCC	-			
36	PB3A	1	PCLK1_1**	Т	PB5B	2	PCLK2_1**		
37	PB3B	1		С	PB5D	2			
38	PB3C	1	PCLK1_0**	Т	PB6B	2	PCLK2_0**		
39	PB3D	1		С	PB6C	2			
40	GND	-			GND	-			
41	VCCIO1	1			VCCIO2	2			

LA-MachXO256 and LA-MachXO640 Logic Signal Connections: 100 TQFP (Cont.)

	LAMXO256				LAMXO640				
Pin Number	Ball Function	Bank	Dual Function	Differential	Ball Function	Bank	Dual Function	Differential	
83	PT4C	0		Т	PT7A	0			
84	GND	-			GND	-			
85	PT4B	0	PCLK0_1**	С	PT6B	0	PCLK0_1**		
86	PT4A	0	PCLK0_0**	T	PT5B	0	PCLK0_0**	С	
87	PT3D	0		С	PT5A	0		Т	
88	VCCAUX	-			VCCAUX	-			
89	PT3C	0		T	PT4F	0			
90	VCC	-			VCC	-			
91	PT3B	0		С	PT3F	0			
92	VCCIO0	0			VCCIO0	0			
93	GNDIO0	0			GNDIO0	0			
94	РТ3А	0		Т	PT3B	0		С	
95	PT2F	0		С	PT3A	0		Т	
96	PT2E	0		Т	PT2F	0		С	
97	PT2D	0		С	PT2E	0		Т	
98	PT2C	0		T	PT2B	0		С	
99	PT2B	0		С	PT2C	0			
100	PT2A	0		Т	PT2A	0		Т	

^{*} NC for "E" devices.

^{**} Primary clock inputs are single-ended.

LA-MachXO640, LA-MachXO1200 and LA-MachXO2280 Logic Signal Connections: 256 ftBGA (Cont.)

		LAM	(O640			LAMXO1200		LAMXO2280						
Ball Number	Ball Function	Bank	Dual Function	Differential	Ball Number	Ball Function	Bank	Dual Function	Differential	Ball Number	Ball Function	Bank	Dual Function	Differential
E11	NC				E11	PT10D	1		С	E11	PT15B	1		С
E10	NC				E10	PT10C	1		Т	E10	PT15A	1		Т
D12	PT9D	0		С	D12	PT10B	1		С	D12	PT14D	1		С
D11	PT9C	0		Т	D11	PT10A	1		Т	D11	PT14C	1		Т
A14	PT7F	0		С	A14	PT9F	1		С	A14	PT14B	1		С
A13	PT7E	0		Т	A13	PT9E	1		Т	A13	PT14A	1		Т
C12	PT8B	0		С	C12	PT9D	1		С	C12	PT13D	1		С
C11	PT8A	0		Т	C11	PT9C	1		Т	C11	PT13C	1		Т
-	-				VCCIO1	VCCIO1	1			VCCIO1	VCCIO1	1		+
-	-				GND	GNDIO1	1			GND	GNDIO1	1		+
B12	PT7B	0		С	B12	PT9B	1		С	B12	PT12D	1		С
B11	PT7A	0		Т	B11	PT9A	1		Т	B11	PT12C	1		Т
A12	PT7D	0		С	A12	PT8F	1		С	A12	PT12B	1		С
A11	PT7C	0		Т	A11	PT8E	1		Т	A11	PT12A	1		Т
GND	GND	-			GND	GND	-			GND	GND	-		
B10	PT5D	0		С	B10	PT8D	1		С	B10	PT11B	1		С
B9	PT5C	0		Т	B9	PT8C	1		Т	B9	PT11A	1		Т
D10	PT8D	0		С	D10	PT8B	1		С	D10	PT10F	1		С
D9	PT8C	0		Т	D9	PT8A	1		Т	D9	PT10E	1		Т
-	-				VCCIO1	VCCIO1	1			VCCIO1	VCCIO1	1		+
-	-				GND	GNDIO1	1			GND	GNDIO1	1		
C10	PT6D	0		С	C10	PT7F	1		С	C10	PT10D	1		С
C9	PT6C	0		Т	C9	PT7E	1		Т	C9	PT10C	1		Т
A9	PT6B	0	PCLK0_1****	С	A9	PT7D	1	PCLK1_1****	С	A9	PT10B	1	PCLK1_1****	С
A10	PT6A	0		Т	A10	PT7C	1		Т	A10	PT10A	1	_	Т
E9	PT9B	0		С	E9	PT7B	1		С	E9	PT9D	1		С
E8	PT9A	0		Т	E8	PT7A	1		Т	E8	PT9C	1		Т
D7	PT5B	0	PCLK0_0****	С	D7	PT6F	0	PCLK1_0****	С	D7	PT9B	1	PCLK1_0****	С
D8	PT5A	0		Т	D8	PT6E	0		Т	D8	PT9A	1		Т
VCCIO0	VCCIO0	0			VCCIO0	VCCIO0	0			VCCIO0	VCCIO0	0		+
GND	GNDIO0	0			GND	GNDIO0	0			GND	GNDIO0	0		+
C8	PT4F	0		С	C8	PT6D	0		С	C8	PT8D	0		С
B8	PT4E	0		Т	B8	PT6C	0		Т	B8	PT8C	0		Т
A8	VCCAUX	-			A8	VCCAUX	-			A8	VCCAUX	-		+
A7	PT4D	0		С	A7	PT6B	0		С	A7	PT7D	0		С
A6	PT4C	0		Т	A6	PT6A	0		Т	A6	PT7C	0		Т
B7	PT4B	0		С	B7	PT5F	0		С	B7	PT7B	0		С
B6	PT4A	0		Т	B6	PT5E	0		Т	B6	PT7A	0		Т
C6	PT3C	0		Т	C6	PT5C	0		Т	C6	PT6A	0		Т
C7	PT3D	0		С	C7	PT5D	0		С	C7	PT6B	0		С
A5	PT3E	0		Т	A5	PT5A	0		Т	A5	PT6C	0		Т
A4	PT3F	0		С	A4	PT5B	0		С	A4	PT6D	0		С
E7	NC				E7	PT4C	0		Т	E7	PT6E	0		Т
E6	NC				E6	PT4D	0		С	E6	PT6F	0		С
B5	PT3B	0		С	B5	PT3F	0		С	B5	PT5D	0		С
B4	PT3A	0		Т	B4	PT3E	0		Т	B4	PT5C	0		T
D5	PT2D	0		С	D5	PT3D	0		С	D5	PT5B	0		С
D6	PT2C	0		T	D6	PT3C	0		T	D6	PT5A	0		T
C4	PT2E	0		T	C4	PT4A	0		Т	C4	PT4A	0		Т
C5	PT2F	0		С	C5	PT4B	0		С	C5	PT4B	0		С
-	-	-			-	-	-			GND	GND	-		1
D4	NC				D4	PT2D	0		С	D4	PT3D	0		С
D3	NC				D3	PT2C	0		Т	D3	PT3C	0		Т

LA-MachXO2280 Logic Signal Connections: 324 ftBGA (Cont.)

Ball Number	Ball Function	LAMXO2280 Bank	Dual Function	Differential
G2	PL11A	6	Buai i unotion	T*
H2	PL11B	6		r C*
L3	PL11C	6		T
L5	PL11D	6		C
H1	PL12A	6		
VCCIO6	VCCIO6	6		
GND	GNDIO6	6		
J2	PL12B	6		C*
L4	PL12C	6		
L6	PL12D	6		C
K2	PL13A	6		
K1	PL13B	6		C*
J1	PL13C	6		T
VCC	VCC	-		·
L2	PL13D	6		С
M5	PL14D	6		C
M3	PL14C	6	TSALL	T
L1	PL14B	6	. 3	
M2	PL14A	6		
M1	PL15A	6		 T*
N1	PL15B	6		C*
M6	PL15C	6		T
M4	PL15D	6		C
VCCIO6	VCCIO6	6		
GND	GNDIO6	6		
P1	PL16A	6		T*
P2	PL16B	6		C*
N3	PL16C	6		Т
N4	PL16D	6		С
GND	GND	-		
T1	PL17A	6	LLM0_PLLT_FB_A	T*
R1	PL17B	6	LLM0_PLLC_FB_A	C*
P3	PL17C	6		Т
N5	PL17D	6		С
R3	PL18A	6	LLM0_PLLT_IN_A	T*
R2	PL18B	6	LLM0_PLLC_IN_A	C*
P4	PL19A	6		Т
N6	PL19B	6		С
U1	PL20A	6		Т
VCCIO6	VCCIO6	6		
GND	GNDIO6	6		
GND	GNDIO5	5		
VCCIO5	VCCIO5	5		

LA-MachXO2280 Logic Signal Connections: 324 ftBGA (Cont.)

		LAMXO2280		
Ball Number	Ball Function	Bank	Dual Function	Differential
V10	PB9B	4		С
N10	PB9C	4		Т
R10	PB9D	4		С
P10	PB10F	4	PCLK4_1**	С
T10	PB10E	4		Т
U10	PB10D	4		С
V11	PB10C	4		Т
U11	PB10B	4	PCLK4_0**	С
VCCIO4	VCCIO4	4		
GND	GNDIO4	4		
T11	PB10A	4		Т
U12	PB11A	4		Т
R11	PB11B	4		С
GND	GND	-		
T12	PB11C	4		Т
P11	PB11D	4		С
V12	PB12A	4		Т
V13	PB12B	4		С
R12	PB12C	4		Т
N11	PB12D	4		С
U13	PB12E	4		Т
VCCIO4	VCCIO4	4		
GND	GNDIO4	4		
V14	PB12F	4		С
T13	PB13A	4		Т
P12	PB13B	4		С
R13	PB13C	4		Т
N12	PB13D	4		С
V15	PB14A	4		Т
U14	PB14B	4		С
V16	PB14C	4		Т
GND	GND	-		
T14	PB14D	4		С
U15	PB15A	4		Т
V17	PB15B	4		С
P13	NC	-		
T15	PB15D	4		
U16	PB16A	4		Т
V18	PB16B	4		С
N13	PB16C	4		T
R14	PB16D	4		С
VCCIO4	VCCIO4	4		
GND	GNDIO4	4		

LA-MachXO2280 Logic Signal Connections: 324 ftBGA (Cont.)

LAMXO2280								
Ball Number	Ball Function	Bank	Dual Function	Differential				
G8	VCCIO0	0						
G7	VCCIO0	0						

^{*} Supports true LVDS outputs.

^{**} Primary clock inputs are single-ended.

Thermal Management

Thermal management is recommended as part of any sound FPGA design methodology. To assess the thermal characteristics of a system, Lattice specifies a maximum allowable junction temperature in all device data sheets. Designers must complete a thermal analysis of their specific design to ensure that the device and package do not exceed the junction temperature limits. Refer to the Thermal Management document to find the device/package specific thermal values.

For Further Information

For further information regarding Thermal Management, refer to the following located on the Lattice website at www.latticesemi.com.

- · Thermal Management document
- Technical Note TN1090 Power Estimation and Management for MachXO Devices
- Power Calculator tool included with Lattice's ispLEVER design tool, or as a standalone download from www.latticesemi.com/software